

# Ashkhen Yesayan

## List of Publications by Year in descending order

Source: <https://exaly.com/author-pdf/2267530/publications.pdf>

Version: 2024-02-01

13  
papers

152  
citations

1684188

5  
h-index

1474206

9  
g-index

13  
all docs

13  
docs citations

13  
times ranked

195  
citing authors

#	ARTICLE	IF	CITATIONS
1	Two-dimensional p-n junction under equilibrium conditions. Semiconductors, 2002, 36, 903-907.	0.5	44
2	Physics-based compact model for ultra-scaled FinFETs. Solid-State Electronics, 2011, 62, 165-173.	1.4	33
3	Charge-Based Modeling of Double-Gate and Nanowire Junctionless FETs Including Interface-Trapped Charges. IEEE Transactions on Electron Devices, 2016, 63, 1368-1374.	3.0	26
4	Explicit drain current model of junctionless double-gate field-effect transistors. Solid-State Electronics, 2013, 89, 134-138.	1.4	16
5	Analytical Modeling of Double-Gate and Nanowire Junctionless ISFETs. IEEE Transactions on Electron Devices, 2020, 67, 1157-1164.	3.0	14
6	The linearly graded two-dimensional p-n junction. Applied Physics Letters, 2004, 84, 3313-3315.	3.3	6
7	Surface Trap-Induced Conductivity Type Switching in Semiconductor Nanowires: Analytical and Numerical Analyses. IEEE Transactions on Electron Devices, 2017, 64, 5249-5255.	3.0	5
8	Multiple quantum well photodiode with lateral p-n-junctions. Thin Solid Films, 2004, 451-452, 389-392.	1.8	3
9	Photocurrent relaxations and gain in semiconductor nanowires. , 2014, , .		3
10	Conductivity type switching in semiconductor nanowires. , 2016, , .		1
11	Critical Radius of Full Depletion in Semiconductor Nanowires Caused by Surface Charge Trapping. Semiconductors, 2018, 52, 2022-2025.	0.5	1
12	Photo-emf in Parabolic Graded-Gap Semiconductors. Physica Status Solidi A, 2001, 184, 433-436.	1.7	0
13	A fully explicit static model for DG JLFET valid in all modes of operation. , 2014, , .		0